

SG100N03S

100V N-Channel Power MOSFET

	SOP-8	D
$ V_{\text{DSS}} , 100V \\ R_{\text{DS(ON)}} , 25m\Omega \text{ (max.) } @ \text{V}_{\text{GS}} = 10V \\ R_{\text{DS(ON)}} , 28m\Omega \text{ (max.) } @ \text{V}_{\text{GS}} = 4.5V \\ I_D , 9.8A $	D D D D D D D D D D D D D D D D D D D	G

Description	Features
The SG100N03S uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	 Motor / Body Load Control Automotive Systems Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG100N03S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parame	Symbol	Value	Unit	
Drain-Source Voltage		VDS	100	V
Gate-Source Voltage		Vgs	±20	V
Drain Current-Continuous	T _A =25°C	1-	9.8	Α
Drain Current-Continuous	T _A =70°C	lD ID	7.9	Α
Drain Current-Pulsed Note 1		Ідм	35	А
Avalanche Current, L=3mH		las	6.5	Α
Avalanche Energy, L=3mH		Eas	63	mJ
Maximum Dawar Dissinction	T _A =25°C		3.1	W
Maximum Power Dissipation	T _A =70°C		2	W
Storage Temperature Range		Tstg	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	Reja	t ≤ 10s	-	-	40	°C/W
Maximum Junction-to-Case	R _{eJC}	Steady State	-	-	25	°C/W



Electrical Characteristics (T_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =80V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage	lgss	$V_{GS}=\pm 20V$, $V_{DS}=0V$	-	-	±100	nA

ON CHARACTERISTICS											
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit					
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.2	1.8	2.5	V					
Drain Source On State Desistance	R _{DS(ON)}	Descent	Descent	Proven	Proven	Proven	V _{GS} =10V, I _{DS} =10A	-	-	25	
Drain-Source On-State Resistance		V _{GS} =4.5V, I _{DS} =8A	-	-	28	mΩ					

DYNAMIC CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	1325	-	
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, f=1MHz	-	110	-	pF
Reverse Transfer Capacitance	Crss		-	64	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	7	-	
Rise Time	tr	V_{GS} =10V, V_{DS} =50V, R_L =5 Ω ,	-	7	-	
Turn-Off Delay Time	$T_{d(off)}$	R _{GEN} =3Ω	-	29	-	ns
Fall Time	tf		-	7	-	
Total Gate Charge at 10V	Qg		-	34	-	
Gate to Source Gate Charge	Q _{gs}	V _{GS} =10V, V _{DS} =50V, I _D =10A	-	6	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	9	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =10A	-	-	1.3	V	
Body Diode Reverse Recovery Time	trr		-	32	-	ns	
Body Diode Reverse Recovery Charge	Qrr	I⊧=10A, dl/dt=500A/µs	-	200	-	nC	

Notes:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

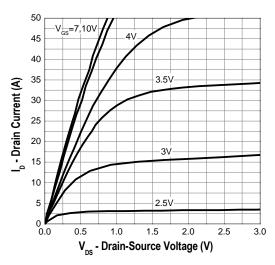
 R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.



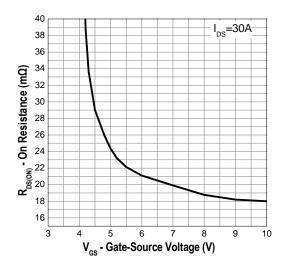
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Typical Operating Characteristics

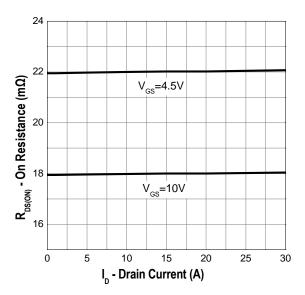
Output Characteristics



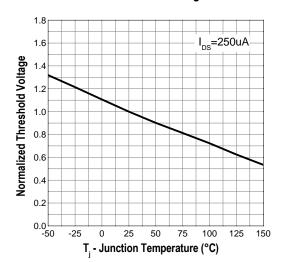
Gate-Source On Resistance



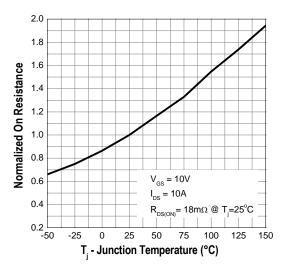
Drain-Source On Resistance



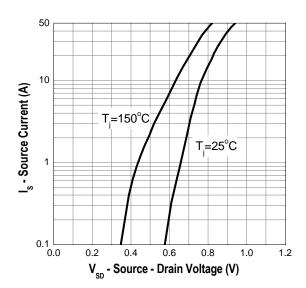
Gate Threshold Voltage



Drain-Source On Resistance

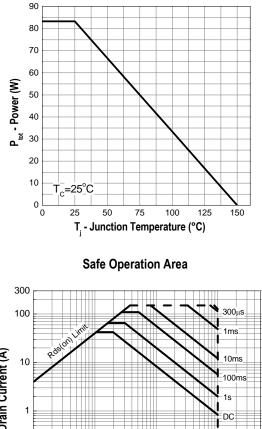




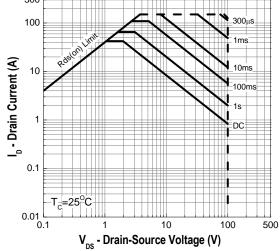




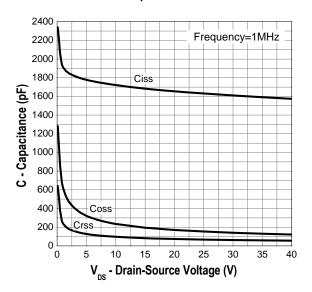
Typical Operating Characteristics (Cont.)

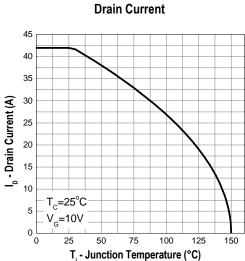


Power Dissipation

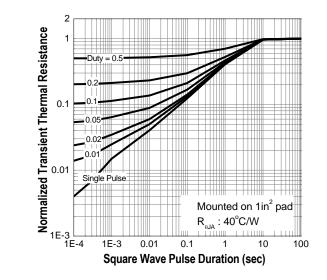


Capacitance

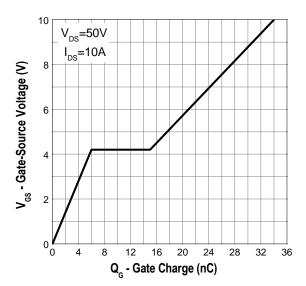




Thermal Transient Impedance



Gate Charge

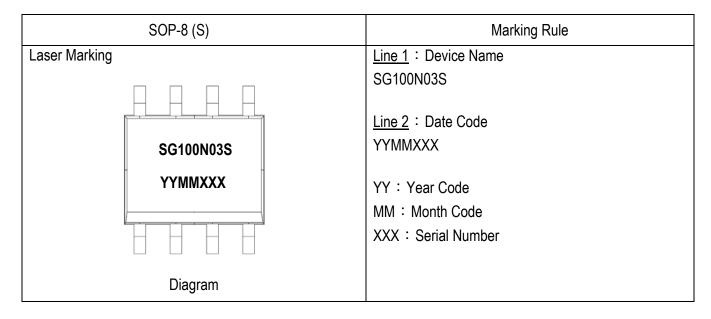


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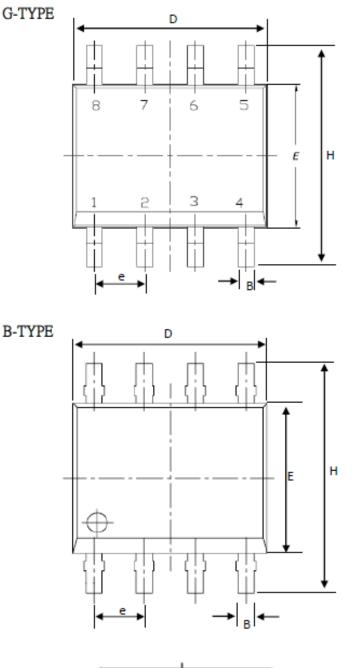


Marking Information





Package of Dimension





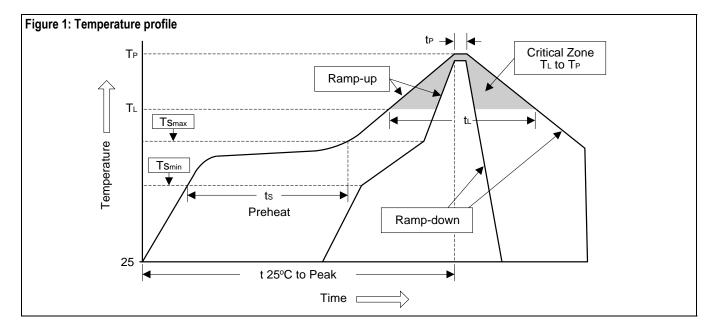
2. Dimension does not include burrs and mold flash/protrusions.

Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
е	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00



Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t⊳)	10 10 50 560	2010 40 360
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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